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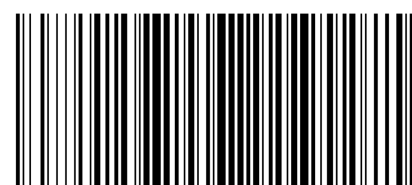

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Surface chemical analysis—Depth Profiling—Measurment of sputtered depth

(ISO/TR 15969:2001,IDT)

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前 言

本标准按照 GB/T 1.1—2009 给出的规则起草。

本标准使用翻译法等同采用 ISO/TR 15969:2001《表面化学分析 深度剖析 溅射深度测量》。

本标准由全国微束标准化技术委员会(SAC/TC 38)提出并归口。

本标准负责起草单位:中山大学、浙江大学、中国科学院大连化学物理研究所。

本标准主要起草人:陈建、张训生、谢方艳、龚力、张卫红、盛世善。